

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,844,604 B2
APPLICATION NO. : 09/776059
DATED : January 18, 2005
INVENTOR(S) : Lee et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4.

Line 52, replace "of 900° C." with -- of 900° C --.

Column 6.

Line 49, replace "can be increased forming" with -- can be lowered forming --.

Line 53, replace "of Al₂O₃as illustrated" with -- of Al₂O₃ as illustrated --.

Line 60, replace "temperature can be increased" with -- temperature can be lowered --.

Line 65, replace "800-850° C. when" with -- 800-850° C when --.

Line 66, replace "can be 900° C. when" with -- can be 900° C when --.

Column 7.

Line 6, replace "can be increased compared" with -- can be reduced compared --.

Lines 61-64, replace "6, which shows the charge pumping current of SiO₂ and Al₂O₃.

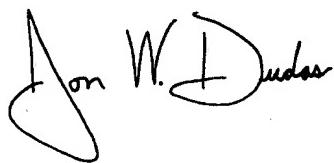
As can be seen, the interface trap density of Al₂O₃ is greater than SiO₂. Such" with
-- 6. Such--.

Column 10.

Line 21, replace "dielectric layer wherein" with -- dielectric layer, wherein --.

Signed and Sealed this

Twenty-seventh Day of June, 2006



JON W. DUDAS
Director of the United States Patent and Trademark Office